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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/857,803	06/11/2001	Hiroji Aga	109725	2312
25944 7:	590 07/15/2003			
OLIFF & BERRIDGE, PLC		EXAMINER		
P.O. BOX 19928			ESTRADA MICUELLE	
ALEXANDRIA	ALEXANDRIA, VA 22320		ESTRADA, MICHELLE	
			ART UNIT	PAPER NUMBER
			2823	
			DATE MAILED: 07/15/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

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onsidered timely. g date of this communication. .C. § 133). uce any					
ion as to the merits is 5. 213.					
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FR 1.85(a).					
the Examiner.					
are Examiner.					
(f).					
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	Application No.	Applicant(s)				
	09/857,803	AGA ET AL.				
Office Action Summary	Examiner	Art Unit				
•	Michelle Estrada	2823				
The MAILING DATE of this communication app						
Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period of the period for reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).				
1)⊠ Responsive to communication(s) filed on <u>12.</u>	lune 2003					
·—	is action is non-final.					
,		osecution as to the merits is				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
	☑ Claim(s) <u>1-9</u> is/are pending in the application.					
	4a) Of the above claim(s) <u>6-9</u> is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.						
	6)⊠ Claim(s) <u>1-5</u> is/are rejected.					
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or election requirement.						
Application Papers	ır					
9) The specification is objected to by the Examiner.						
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11) The proposed drawing correction filed on	is: a) approved b) disappro					
If approved, corrected drawings are required in reply to this Office action.						
12) The oath or declaration is objected to by the Examiner.						
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a) All b) Some * c) None of:						
1. Certified copies of the priority document						
2. Certified copies of the priority documents have been received in Application No						
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
14) Acknowledgment is made of a claim for domesti	ic priority under 35 U.S.C. § 119(e) (to a provisional application).				
 a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121. 						
Attachment(s)						
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal	y (PTO-413) Paper No(s) Patent Application (PTO-152)				
S. Patent and Trademark Office						

Application/Control Number: 09/857,803

Art Unit: 2823

DETAILED ACTION

The final action mailed 3/12/03 is withdrawn in view of the new grounds of rejection.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1 and 2 are rejected under 35 U.S.C. 103(a) as being unpatentable over the combination of Yamamoto (JP-10275905) and Sato (US 2002/0127820).

Yamamoto discloses a method for producing an SOI wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer (5) and a bond wafer (1) having a micro bubble layer formed by gas ion implantation (See fig. 1c) and a step of delaminating a wafer having an SOI layer (2) at the micro bubble layer as a border, wherein, after the delamination step, the wafer having an SOI layer is subjected to a hydrogen RTA treatment.

Yamamoto does not disclose cooling the wafer, and a heat treatment of a batch furnace.

Sato discloses a semiconductor substrate (10); forming an insulating layer (14); implanting hydrogen ions into the semiconductor surface; semiconductor substrate (10) is joined to a support substrate (13); the resulting structure is subject to thermal

Application/Control Number: 09/857,803

Art Unit: 2823

treatment for delamination (Page 17, Paragraph [0271]; and after delamination the laminate is set in a hydrogen annealing furnace and subjected to heat treatment (Page 17, Paragraph [0273]. The combination teaches annealing by either furnace or RTA. It would have been within the scope of one of ordinary skill in the art to use either one (furnace or RTA) for the first part of the heating step and the other one for the rest of the heating step. A cooling step would occur after RTA treatment upon removal of the light source.

It would have been within the scope of one of ordinary skill in the art to combine the teachings of Yamamoto and Sato to enable formation of part of the heat treatment of Yamamoto. Also, It would have been within the scope of one of ordinary skill in the art to use hydrogen in the heating step of Sato because it would be use to eliminate the roughness in the surface of the wafer after the delamination step as described by Yamamoto.

Claims 3-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over the combination of Yamamoto and Sato as applied to claims 1 and 2 above, and further in view of Adachi et al. (6,074,479) and Wolf et al. (Vol. 1).

The combination of Yamamoto and Sato does not disclose that the wafer is a CZ wafer of which COPs (Crystal Originated Particles) at least on surface are reduced is used as the bond wafer, and that the CZ wafer is produced from a single crystal ingot.

Adachi et al. discloses a wafer, which is a CZ wafer of which COPs (Crystal Originated Particles) at least on surface are reduced (Col. 1, lines 25-30). It would have

Application/Control Number: 09/857,803

Art Unit: 2823

been within the scope of one of ordinary skill in the art to employ the CZ wafer of Adachi

et al. to provide the bond wafer of the combination and further enhance quality of the

product.

Wolf et al. (Vol. 1) discloses that the CZ wafer can be produced from a single

crystal ingot (See pages 23-25).

It would have been within the scope of one of ordinary skill in the art to produce

the CZ wafer of Wolf (Vol. 1) to enable the bond wafer of the combination of Yamamoto,

Sato and Adachi et al. to be provided.

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Michelle Estrada whose telephone number is (703) 308-

0729. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone numbers

for the organization where this application or proceeding is assigned are 703-308-7722

for regular communications and 703-308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or

proceeding should be directed to the receptionist whose telephone number is 703-308-

0956.

George/Fourson
Primary Examiner

Page 4

Art Unit 2823

MEstrada July 8, 2003